

High Voltage Thyristor \ Diode Module

$$V_{RRM} = 2 \times 2000 \text{ V}$$

$$I_{TAV} = 250 \text{ A}$$

$$V_T = 1,03 \text{ V}$$

Phase leg

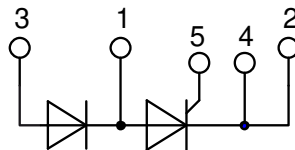
Part number

MCD224-20io1



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				2100	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				2000	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 2000\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	mA
		$V_{R/D} = 2000\text{ V}$	$T_{VJ} = 140^{\circ}\text{C}$			40	mA
V_T	forward voltage drop	$I_T = 250\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,08	V
		$I_T = 500\text{ A}$				1,31	V
		$I_T = 250\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1,03	V
		$I_T = 500\text{ A}$				1,33	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 140^{\circ}\text{C}$			250	A
$I_{T(RMS)}$	RMS forward current	180° sine				390	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}\text{C}$			0,72	V
r_T	slope resistance					1,2	mΩ
R_{thJC}	thermal resistance junction to case					0,139	K/W
R_{thCH}	thermal resistance case to heatsink				0,04		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			820	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			8,00	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			8,64	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			6,80	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			7,35	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			320,0	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			310,5	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			231,2	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			224,4	kA ² s
C_J	junction capacitance	$V_R = 700\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		235		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^{\circ}\text{C}$			120	W
		$t_p = 500\text{ }\mu\text{s}$				60	W
P_{GAV}	average gate power dissipation					20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 750\text{ A}$				100	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 1\text{ A}/\mu\text{s};$ $I_G = 1\text{ A}; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 250\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}\text{C}$			1000	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2	V
			$T_{VJ} = -40^{\circ}\text{C}$			3	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
			$T_{VJ} = -40^{\circ}\text{C}$			220	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			0,25	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
		$I_G = 0,45\text{ A}; di_G/dt = 0,45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0,5\text{ A}; di_G/dt = 0,5\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 250\text{ A}; V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 50\text{ V}/\mu\text{s}; t_p = 200\text{ }\mu\text{s}$			350		μs

Package Y1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			600	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				680		g
M_D	mounting torque		4,5		7	Nm
M_T	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	16,0			mm
$d_{Spb/Apb}$		terminal to backside	16,0			mm
V_{ISOL}	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD224-20io1	MCD224-20io1	Box	3	481238

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140^{\circ}\text{C}$



Thyristor

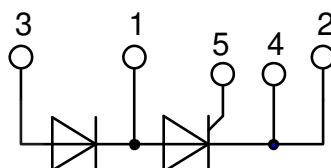
$V_{0\max}$	threshold voltage	0,72	V
$R_{0\max}$	slope resistance *	1,01	mΩ

Outlines Y1

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



Thyristor

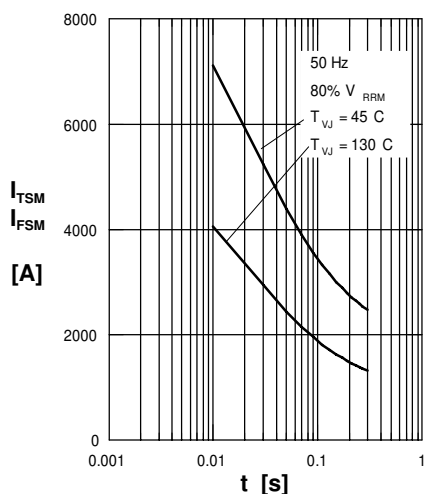


Fig. 1 Surge overload current
 $I_{T(F)SM}$: crest value, t : duration

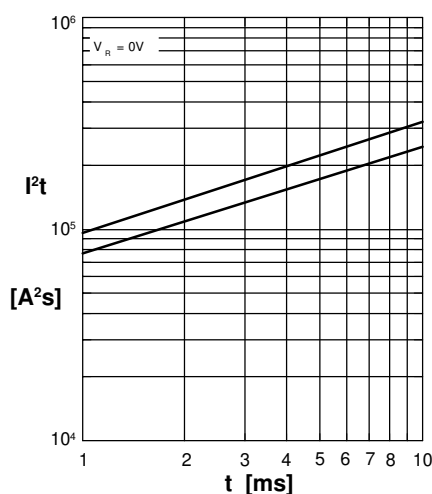


Fig. 2 I^2t versus time (1-10 ms)

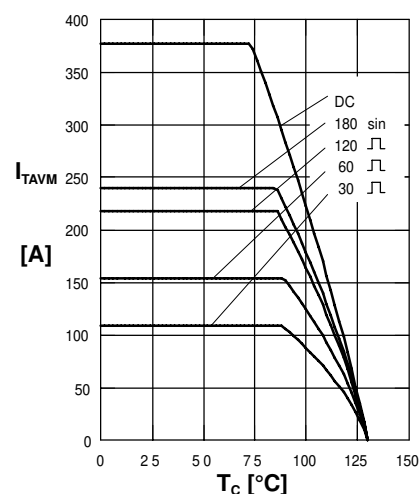


Fig. 3 Max. forward current
 at case temperature

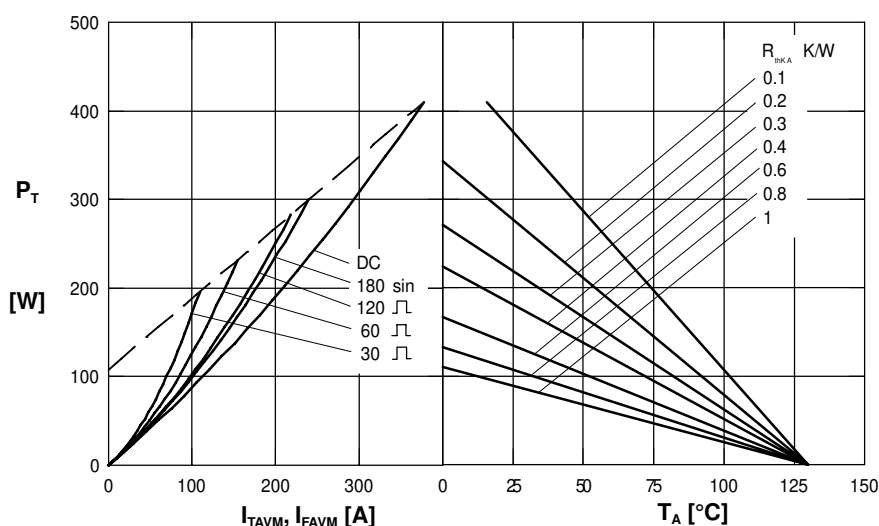


Fig. 4 Power dissipation versus onstate current and
 ambient temperature (per thyristor/diode)

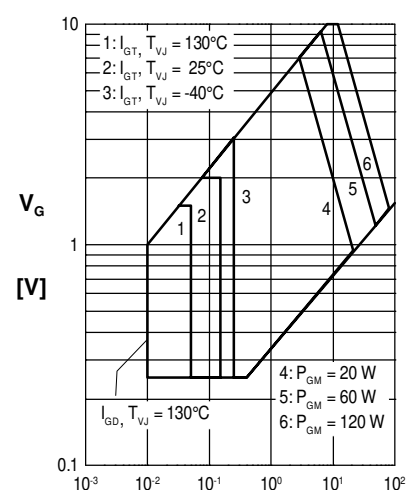


Fig. 5 Gate trigger characteristics

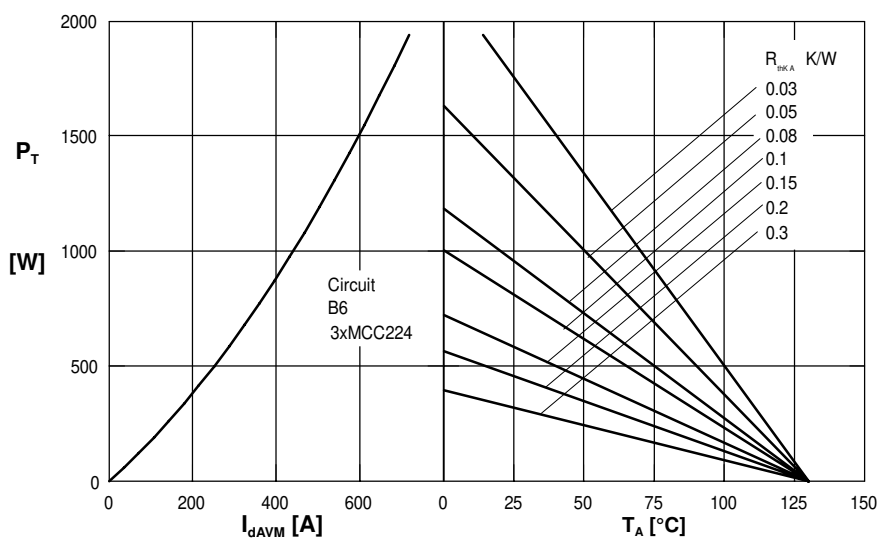


Fig. 6 Three phase rectifier bridge: Power dissipation versus
 direct output current and ambient temperature

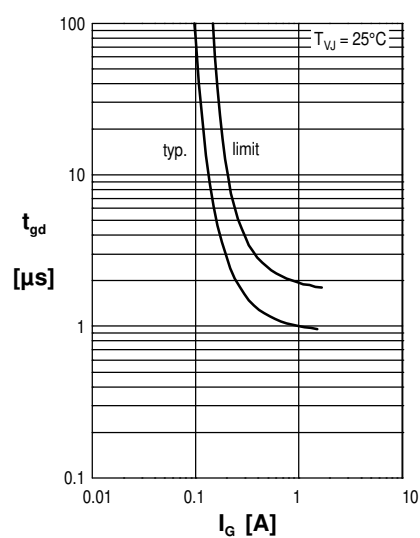


Fig. 7 Gate trigger delay time

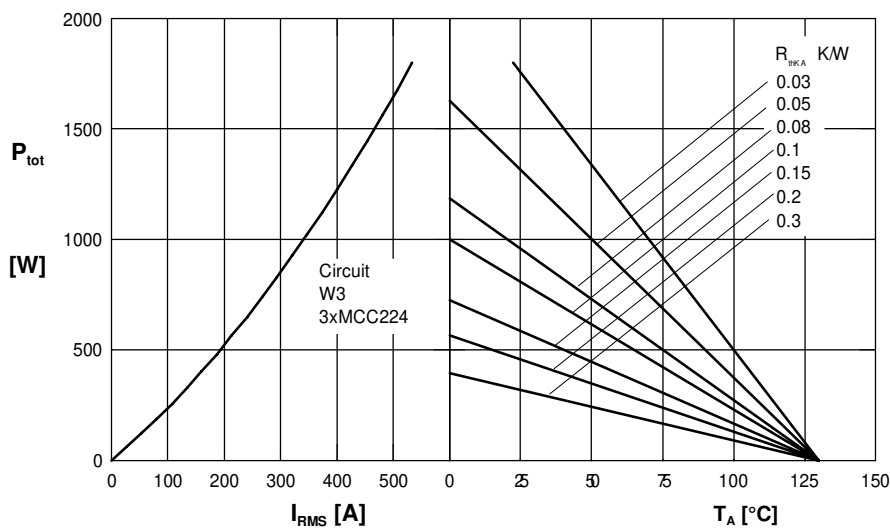
Rectifier


Fig. 7 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

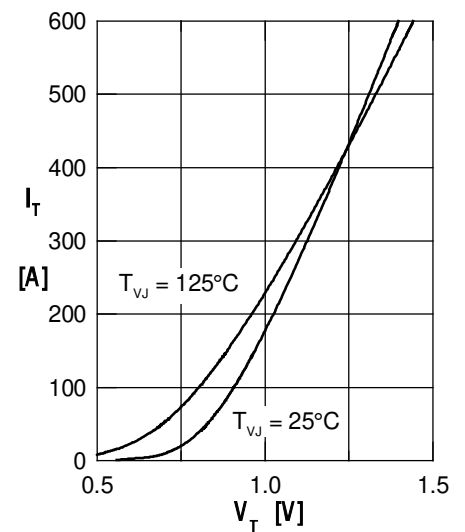


Fig. 10 Forward characteristics

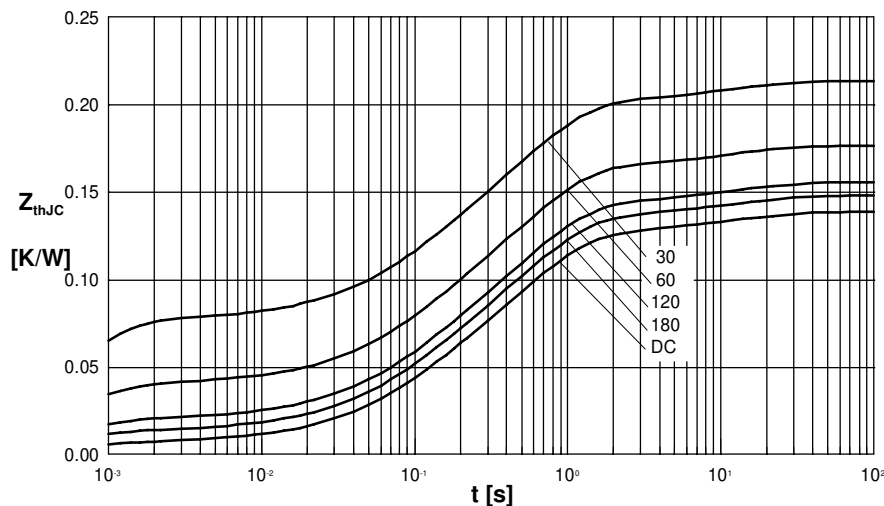


Fig. 8 Transient thermal impedance junction to case (per thyristor/diode)

R_{thJC} for various conduction angles d :

d	R_{thJC} [K/W]
DC	0.139
180°C	0.148
120°C	0.156
60°C	0.176
30°C	0.214

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0067	0.00054
2	0.0358	0.098
3	0.0832	0.540
4	0.0129	12.00

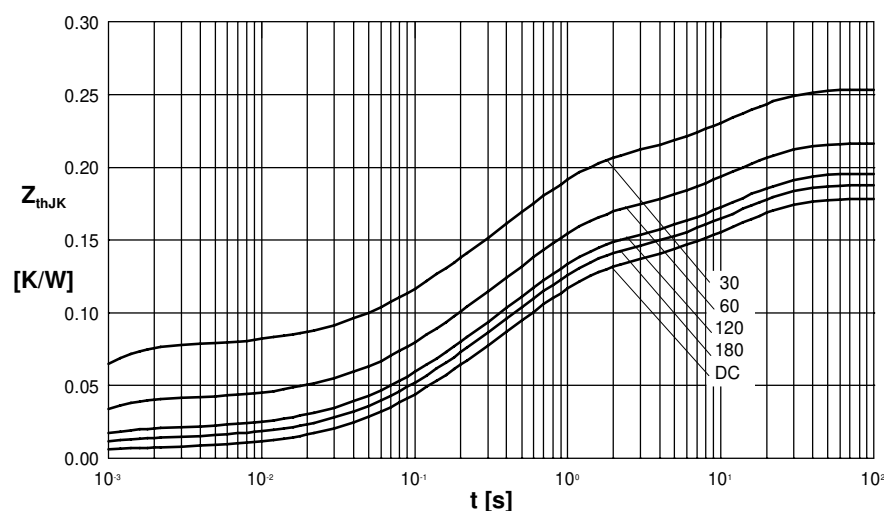


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor/diode)

R_{thJK} for various conduction angles d :

d	R_{thJK} [K/W]
DC	0.179
180°C	0.188
120°C	0.196
60°C	0.216
30°C	0.256

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0067	0.001
2	0.0358	0.080
3	0.0832	0.200
4	0.0129	1.000